

# **isc Silicon PNP Darlington Power Transistor**

**BD898** 

### **DESCRIPTION**

- · Collector-Emitter Breakdown Voltage-
  - : V<sub>(BR)CEO</sub>= -60V(Min)
- · High DC Current Gain
  - : h<sub>FE</sub>= 750(Min) @I<sub>C</sub>= -3A
- · Collector Power Dissipation-
  - : P<sub>C</sub>= 70W@ T<sub>C</sub>= 25℃
- 8 A Continuous Collector Current
- Complement to Type BD897
- Minimum Lot-to-Lot variations for robust device performance and reliable operation



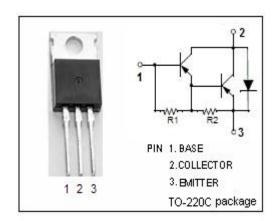
 Designed for use as complementary AF push-pull output stage applications

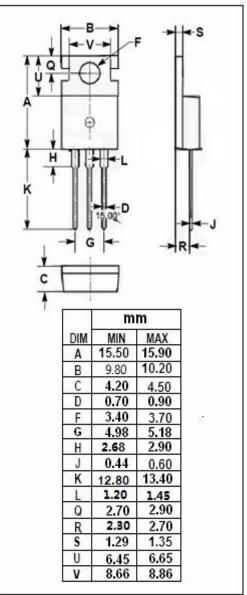
ABSOLUTE MAXIMUM RATINGS(Ta=25℃)

ABOOLOTE MAXIMOM (ATMOS(Ta=25 C)						
SYMBOL	PARAMETER	VALUE	UNIT			
$V_{CBO}$	Collector-Base Voltage	-60	V			
V <sub>CEO</sub>	Collector-Emitter Voltage	-60	V			
V <sub>EBO</sub>	Emitter-Base Voltage	-5	V			
Ic	Collector Current-Continuous	-8	Α			
I <sub>B</sub>	Base Current-Continuous	-0.3	Α			
Pc	Collector Power Dissipation @ T <sub>a</sub> =25℃	2	10/			
	Collector Power Dissipation @ T <sub>c</sub> =25℃	70	W			
TJ	Junction Temperature 150		$^{\circ}$ C			
T <sub>stg</sub>	Storage Temperature Range	-65~150	$^{\circ}$			

### THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	MAX	UNIT
R <sub>th j-c</sub>	Thermal Resistance,Junction to Case	1.79	°C/W
R <sub>th j-a</sub>	R <sub>th j-a</sub> Thermal Resistance,Junction to Ambient		°C/W







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### **ELECTRICAL CHARACTERISTICS**

T<sub>C</sub>=25℃ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V <sub>(BR)CEO</sub>	Collector-Emitter Breakdown Voltage	I <sub>C</sub> = -50mA; I <sub>B</sub> = 0	-60			V
V <sub>CE(sat)</sub>	Collector-Emitter Saturation Voltage	I <sub>C</sub> = -3A; I <sub>B</sub> = -12mA			-2.5	V
V <sub>BE(on)</sub>	Base-Emitter On Voltage	I <sub>C</sub> = -3A ; V <sub>CE</sub> = -3V			-2.5	V
Ісво	Collector Cutoff Current	V <sub>CB</sub> = -60V; I <sub>E</sub> = 0			-0.2	- mA
		V <sub>CB</sub> = -60V; I <sub>E</sub> = 0; T <sub>C</sub> = 100 ℃			-2.0	MA
Iceo	Collector Cutoff Current	V <sub>CE</sub> = -30V; I <sub>B</sub> = 0			-0.5	mA
I <sub>EBO</sub>	Emitter Cutoff Current	V <sub>EB</sub> = -5V; I <sub>C</sub> = 0			-2	mA
h <sub>FE</sub>	DC Current Gain	Ic= -3A; Vc== -3V	750			

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